Electronic Supplementary Information for

## High-performing near-infrared organic phototransistors based on diketopyrrolopyrrole conjugated polymers with partial removal of long branched alkyl side chains

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Figure S1. Absorption spectra of the copolymers **P0**, **P1**, and **P2** (a) in dilute chlorobenzene solutions and (b) as thin films.



Figure S2. Electroluminescence spectrum of the 870 nm NIR LED.



Figure S3. Transfer curves of the NIR OPTs measured alternately for three times before and after the exposure to the NIR light.



Figure S4. Positive shift of the threshold voltage ( $V_{Th}$ ) under NIR light for the NIR OPTs based on (a) **P0**, (b) **P1**, and (c) **P2**.



Figure S5. Transfer characteristics of the NIR OPTs based on (a, d) **P0**, (b, e) **P1**, and (c, f) **P2** in dark and under different NIR intensities ( $V_{DS} = -40V$ )



Figure S6. The calculated EQE as a function of  $V_G$  under different NIR intensities for the NIR OPTs based on (a) **P0**, (b) **P1**, and (c) **P2**. (d) EQE of the three NIR OPTs as a function of NIR power intensity at  $V_G = -10$  V. The EQE were calculated based on the equation of EQE=(hc/ $\lambda q$ )•*R*.



Figure S7. Transfer characteristics of the **P1**:PC<sub>61</sub>BM-based NIR OPTs in dark and under different NIR intensities. The device exhibited a stable and reversible response to NIR light with different intensities from 0.008 to 1.101 mW cm<sup>-2</sup> (red arrow) and then from 1.101 to 0.008 mW cm<sup>-2</sup> (blue arrow).



Figure S8. Photoresponse behaviors of the NIR OPTs based on P1:PC<sub>61</sub>BM (32:1, *by weight*) under ultralow NIR light intensity of 0.002 mW cm<sup>-2</sup>. (a) Transfer curves of the OPTs in dark and under NIR light illumination; (b) corresponding R and  $D^*$  as a function of  $V_G$ .



Figure S9. The calculated (a)  $\mathbf{R}$  and (b) EQE as a function of  $V_{\rm G}$  under different NIR intensities for the NIR OPTs based on **P1**:PC<sub>61</sub>BM (32:1, *by weight*).



Figure S10. The calculated  $D^*$  as a function of  $V_G$  under different NIR intensities for the NIR OPTs based on **P1**:PC<sub>61</sub>BM (32:1, *by weight*).